

General Description

The MY30P03NE5 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

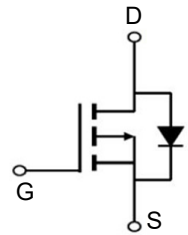
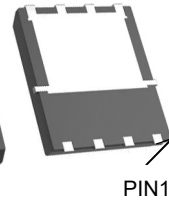


Features

V_{DS}	-30	X
V_{GS}	-30	C
$I_{D@T_A=25^\circ C}$	17	o á
$I_{D@T_A=70^\circ C}$	26	o á

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY30P03NE5	PDFN5*6-8L	018DP	5000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	+20	V
$I_{D@T_A=25^\circ C}$	Drain Current ³ , V_{GS} @ 10V	-30	A
$I_{D@T_A=70^\circ C}$	Drain Current ³ , V_{GS} @ 10V	-8.7	A
IDM	Pulsed Drain Current ¹	-40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	3.57	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
Rthj-c	Maximum Thermal Resistance, Junction-case	6	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	35 $^\circ C/W$	

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-10A	-	17	21	mΩ
		V _{GS} =-4.5V, I _D =-6A	-	26	36	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	1.95	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-6A	-	15	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-30	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-6A	-	15	24	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	8	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V	-	12	-	ns
t _r	Rise Time	I _D =-1A	-	7.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	39	-	ns
t _f	Fall Time	V _{GS} =-10V	-	21	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1260	2000	pF
C _{oss}	Output Capacitance	V _{DS} =-15V f=1.0MHz	-	245	-	pF
C _{rss}	Reverse Transfer Capacitance		-	210	-	pF
t _{rr}	Reverse Recovery Time	I _S =-6A, V _{GS} =0V, dI/dt=100A/μs	-	19	-	ns
Q _{rr}	Reverse Recovery Charge		-	10	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test

Typical Characteristics

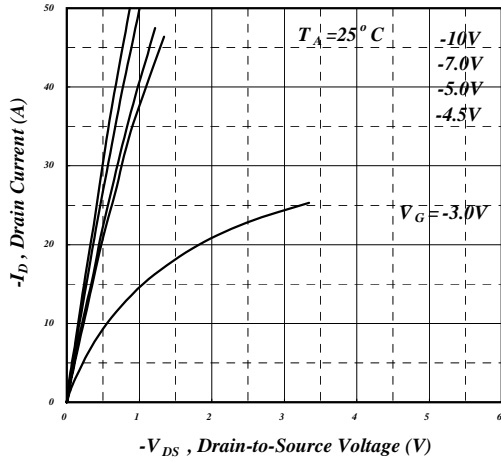


Fig 1. Typical Output Characteristics

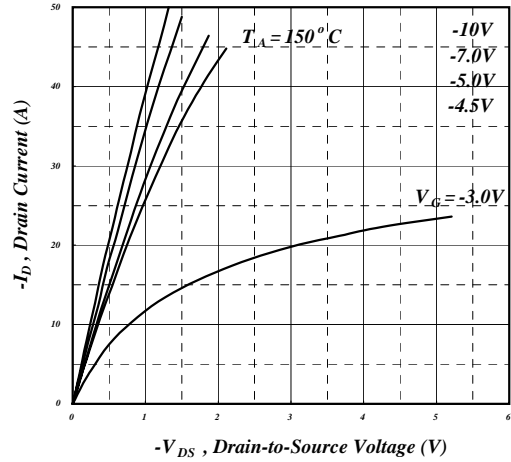


Fig 2. Typical Output Characteristics

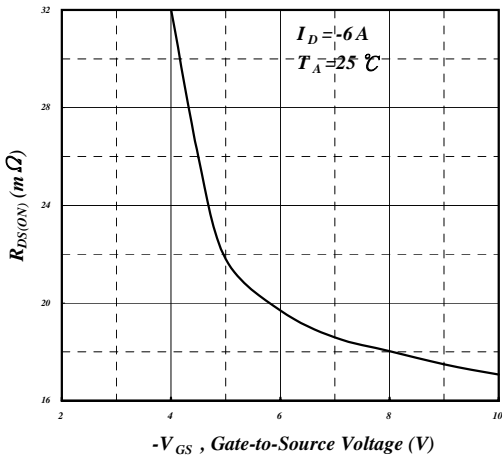


Fig 3. On-Resistance v.s. Gate Voltage

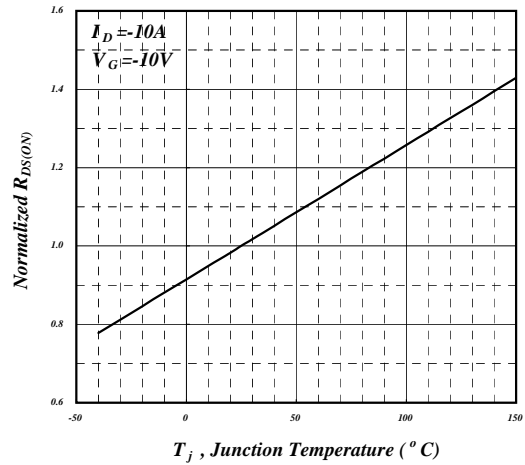


Fig 4. Normalized On-Resistance v.s. Junction Temperature

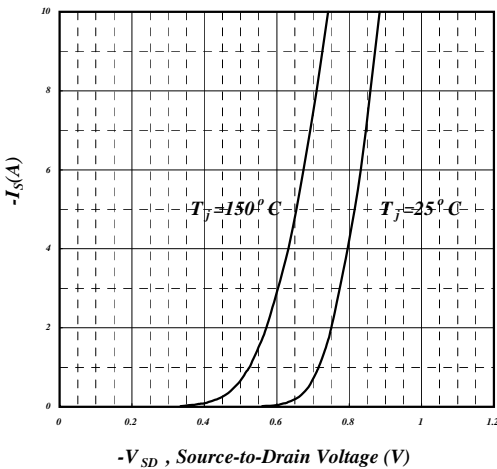


Fig 5. Forward Characteristic of Reverse Diode

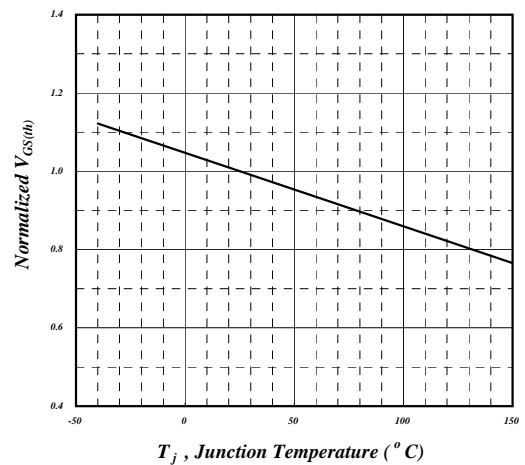


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

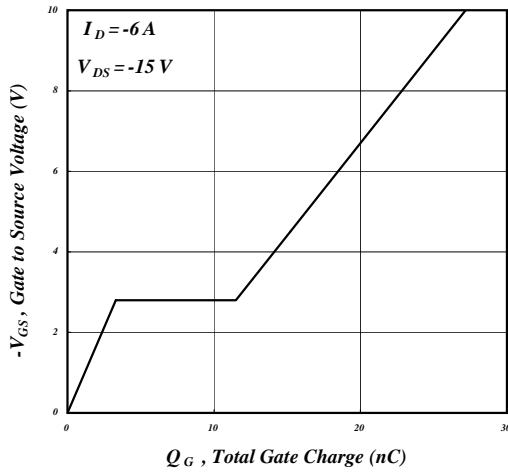


Fig 7. Gate Charge Characteristics

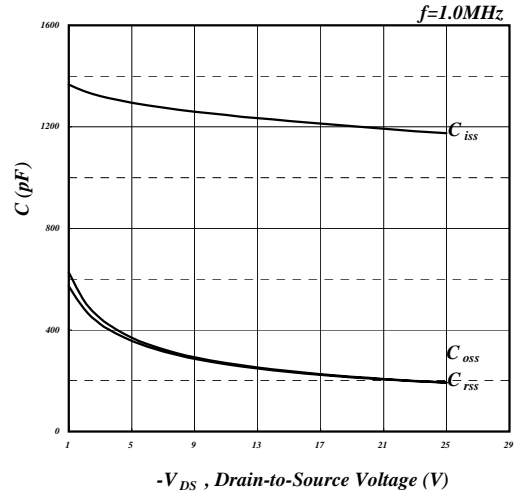


Fig 8. Typical Capacitance Characteristics

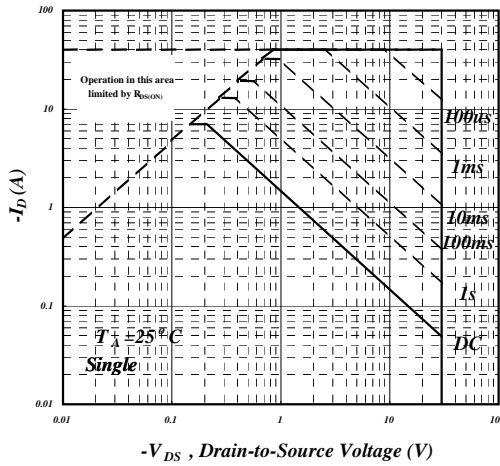


Fig 9. Maximum Safe Operating Area

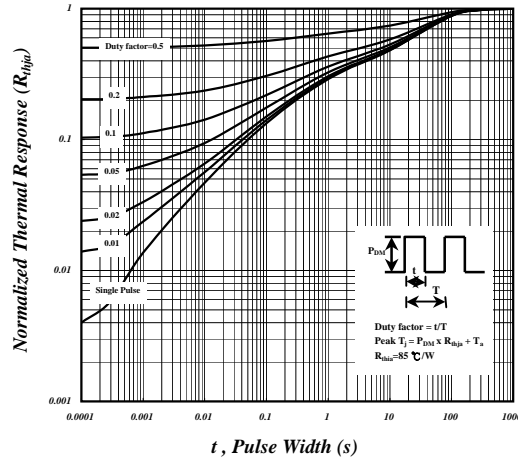


Fig 10. Effective Transient Thermal Impedance

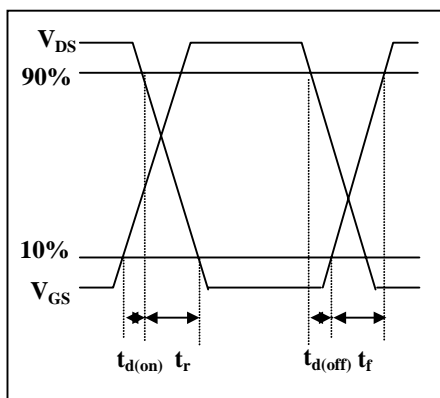


Fig 11. Switching Time Waveform

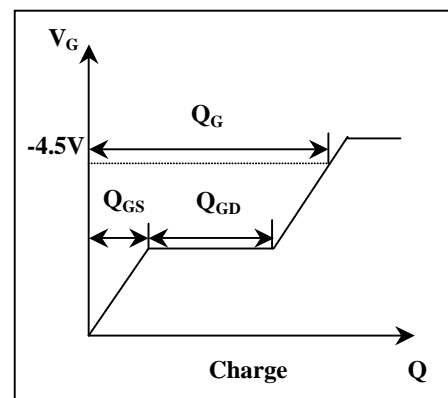
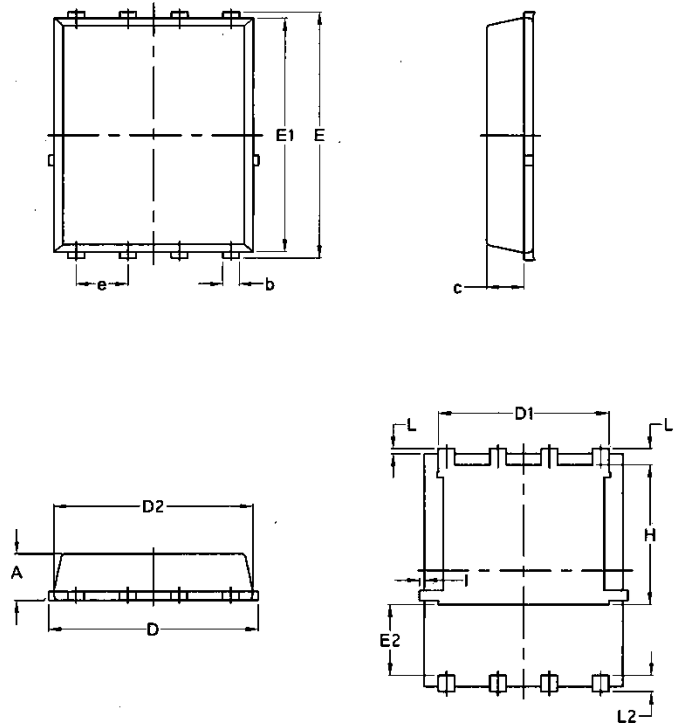


Fig 12. Gate Charge Waveform

Package Mechanical Data-DFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070